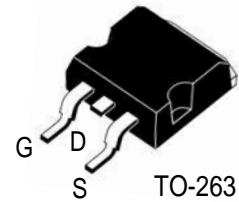
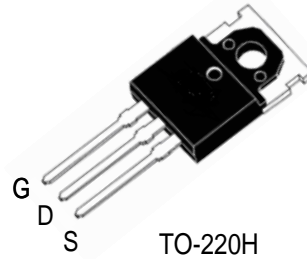


POWER MOSFET

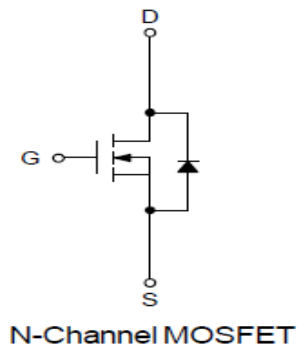
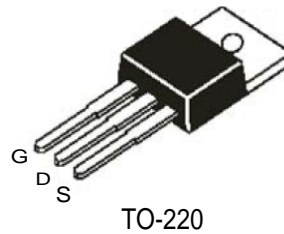
Features

- 68V,75A N-Channel MOSFET
- $R_{DS(on)(typ.)}=6.5m\ \Omega$ @ $V_{GS}=10V$
- High ruggedness
- Fast switching
- 100% avalanche tested
- Exceptional dv/dt capability



Applications

- Switching application



Absolute Maximum Ratings

| Symbol | Parameter | Value | Units |
|-----------|---|-------------|------------|
| V_{DSS} | Drain-Source Voltage | 68 | V |
| V_{GS} | Gate-Source Voltage | ± 25 | V |
| I_D | Continuous Drain Current($T_C=25^\circ C$) | 75 | A |
| | Continuous Drain Current($T_C=100^\circ C$) | 50 | A |
| I_{DM} | Pulsed Drain Current(Note 1) | 240 | A |
| EAS | Single Pulsed Avalanche Energy(Note 2) | 256 | mJ |
| P_D | Maximum Power Dissipation ($T_C=25^\circ C$) | 65 | W |
| | Maximum Power Dissipation ($T_C=100^\circ C$) | 32 | W |
| T_J | Operating Junction Temperature Range | -55 to +175 | $^\circ C$ |
| T_{STG} | Storage Temperature Range | -55 to +175 | $^\circ C$ |

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. Starting $T_J=25^\circ C$, $L=1.0mH$, $R_G=50\ \Omega$, $I_D=37A$, $V_{GS}=10V$



Thermal data

| Symbol | Parameter | Max. | Units |
|-------------|--------------------------------------|------|---------------|
| R_{thJ-C} | Thermal Resistance, Junction to case | 2.2 | $^{\circ}C/W$ |
| | | | |
| | | | |

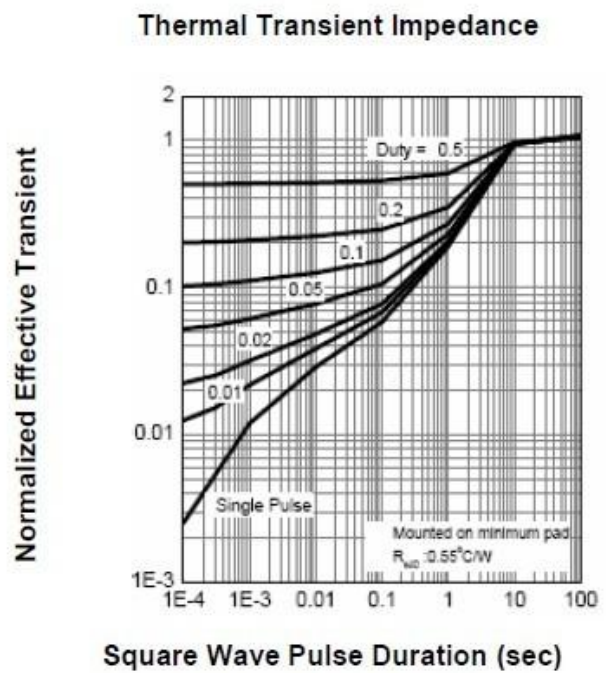
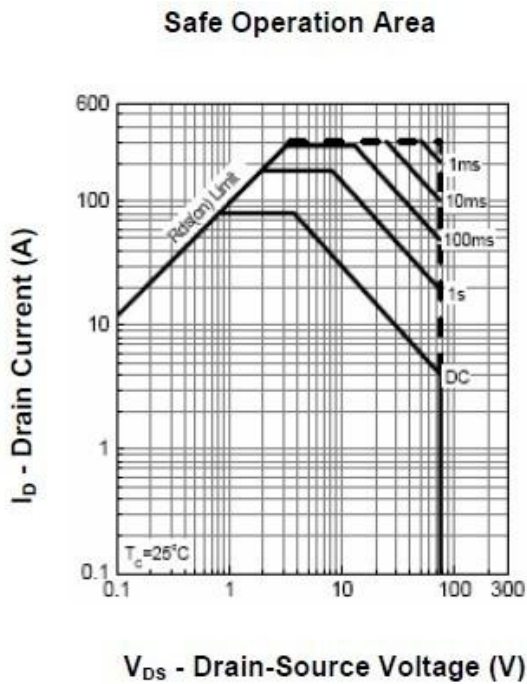
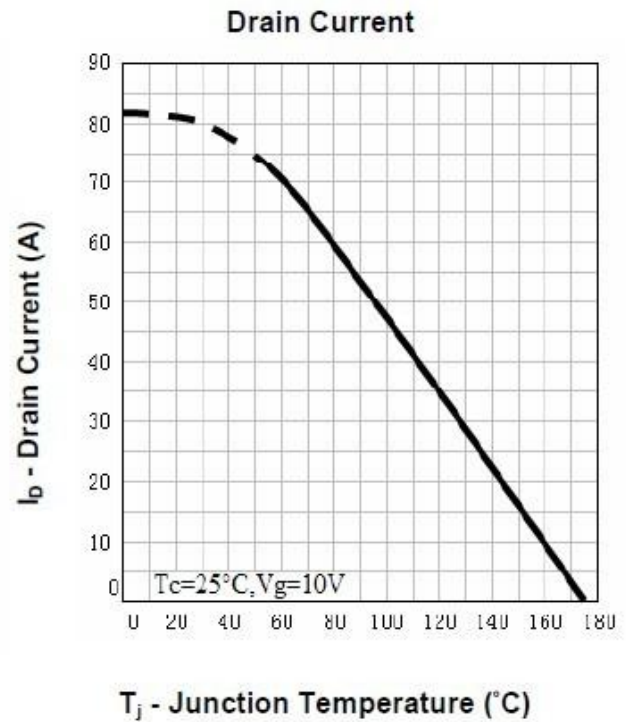
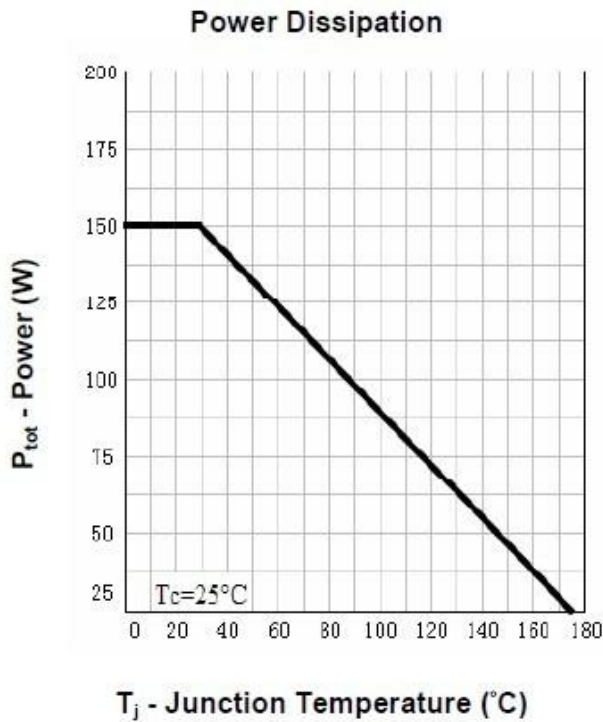
Electrical Characteristics ($T_C=25^{\circ}C$ unless otherwise noted)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|--------------|--------------------------------------|--|------|------|------|------------|
| BV_{DSS} | Drain-Source Breakdown Voltage | $V_{GS}=0V, I_D=250\mu A$ | 68 | | | V |
| I_{DSSS} | Drain-Source Leakage Current | $V_{DS}=68V, V_{GS}=0V$ | | | 1 | μA |
| I_{GSS} | Gate Leakage Current, Forward | $V_{GS}=25V, V_{DS}=0V$ | | | 100 | nA |
| | Gate Leakage Current, Reverse | $V_{GS}= -25V, V_{DS}=0V$ | | | -100 | nA |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{GS}=V_{DS}, I_D=250\mu A$ | 2 | 3 | 4 | V |
| $R_{DS(on)}$ | Collector-Emitter Saturation Voltage | $V_{GS}=10V, I_D=40A$ | | 6.5 | 8 | m Ω |
| gfs | Forward Transconductance | $V_{DS}=15V, I_D=30A$ | | 28 | | S |
| Q_g | Total Gate Charge | $V_{DD}=68V$ $V_{GS}=10V$ $I_D=40A$ | | 76 | | nC |
| Q_{gs} | Gate-Source Charge | | | 17 | | nC |
| Q_{gd} | Gate-Drain Charge | | | 24 | | nC |
| $t_{d(on)}$ | Turn-on Delay Time | $V_{DD}=35V$ $V_{GS}=10V$ $I_D=25A$ $R_G=3.5\Omega$ | - | 37 | - | ns |
| t_r | Turn-on Rise Time | | - | 35 | - | ns |
| $t_{d(off)}$ | Turn-off Delay Time | | - | 110 | - | ns |
| t_f | Turn-off Fall Time | | - | 77 | - | ns |
| C_{iss} | Input Capacitance | $V_{DS}=30V$ $V_{GS}=0V$ $f = 1MHz$ | - | 3250 | - | pF |
| C_{oss} | Output Capacitance | | - | 580 | - | pF |
| C_{rss} | Reverse Transfer Capacitance | | - | 165 | - | pF |
| R_{Gint} | Integrated gate resistor | | | 1.5 | | Ω |

Source-Drain Ratings and Characteristics ($T_C=25^{\circ}C$ unless otherwise noted)

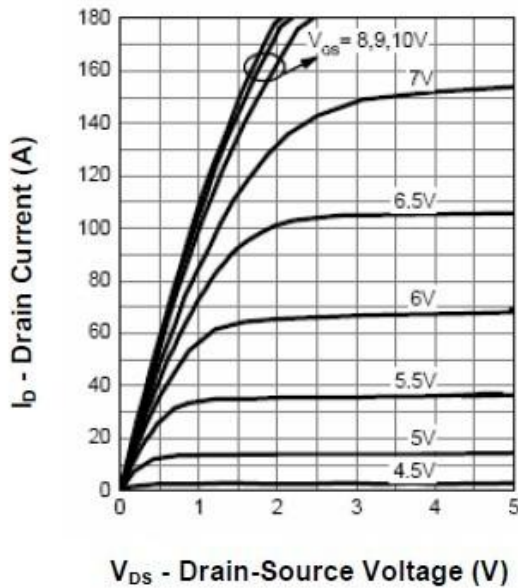
| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|----------|----------------------------------|---|------|------|------|-------|
| V_{SD} | Forward On Voltage | $V_{GS}=0V, I_S=20A$ | - | | 1.2 | V |
| I_S | Continuous Diode Forward Current | | | | 85 | A |
| t_{rr} | Reverse Recovery Time | $V_{DD}=25V, I_S=40A$ $di_F/dt=100A/\mu s$ | - | 42 | | ns |
| Q_{rr} | Reverse Recovery Charge | | - | 70 | | nC |

Typical Characteristics

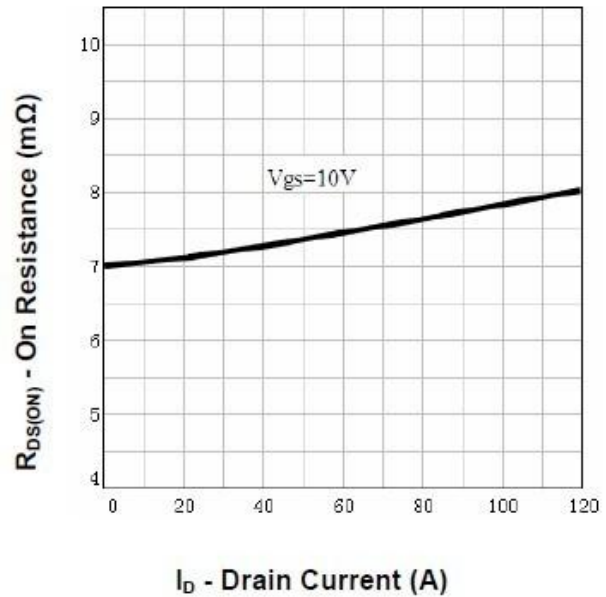


Typical Characteristics

Output Characteristics

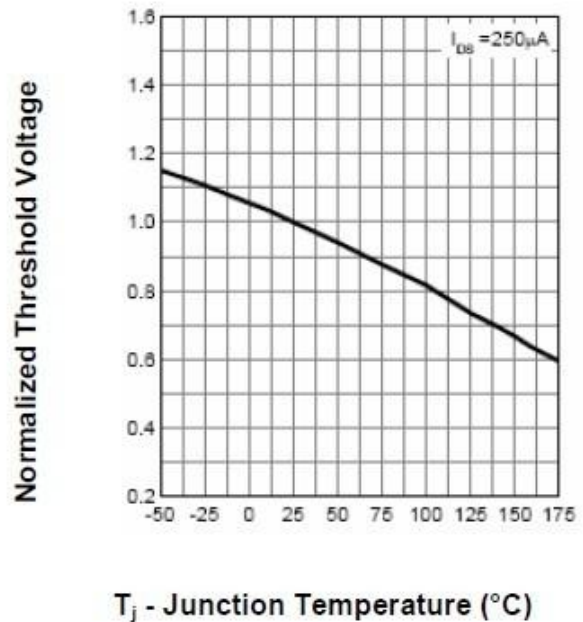
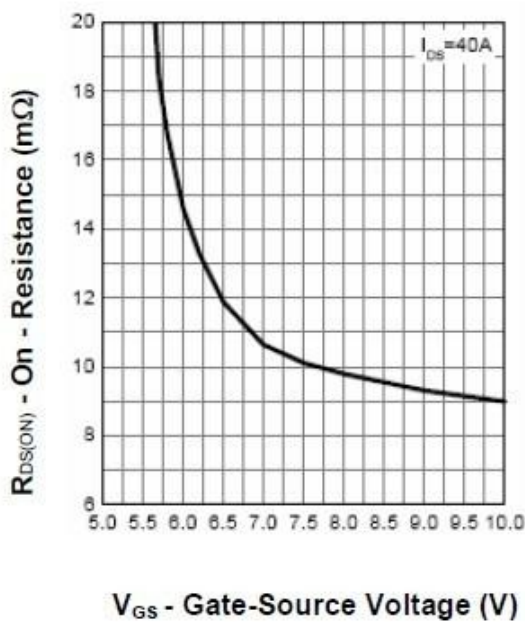


Drain-Source On Resistance

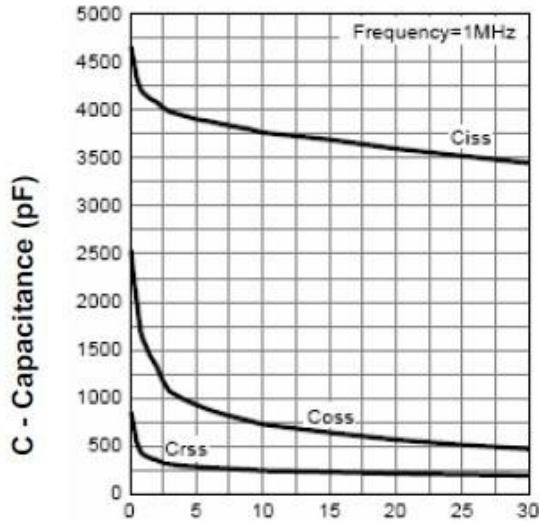


Drain-Source On Resistance

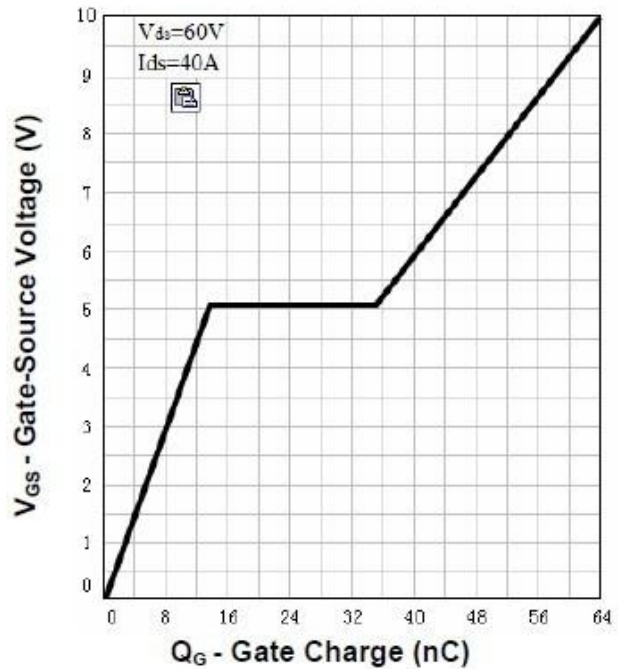
Gate Threshold Voltage



Capacitance

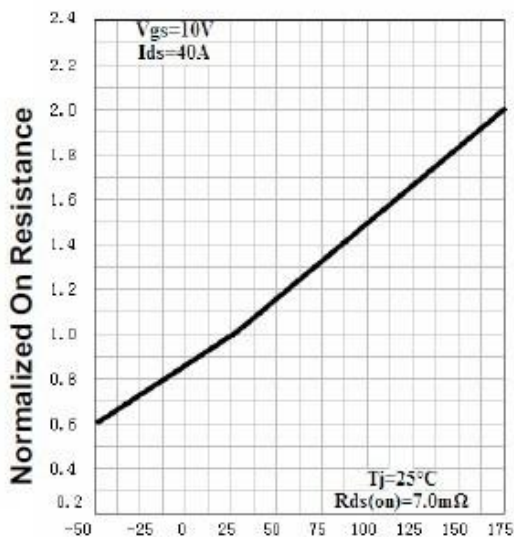


Gate Charge

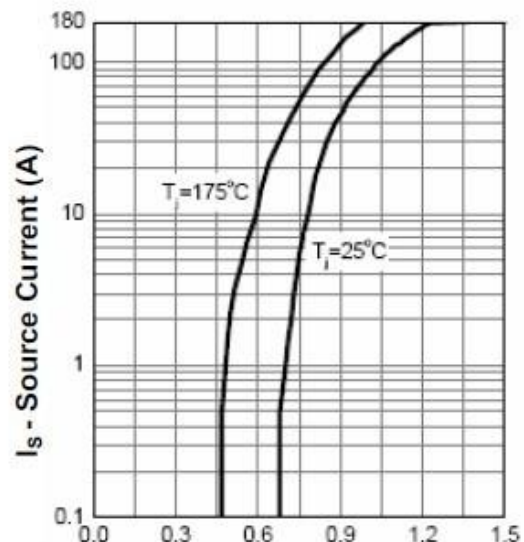


Typical Characteristics

Drain-Source On Resistance

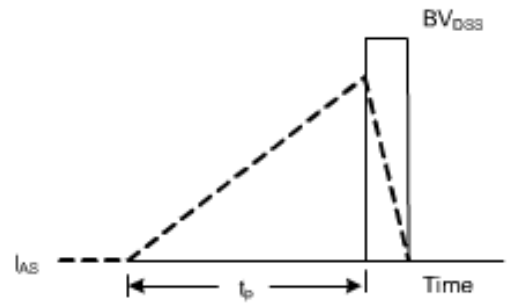
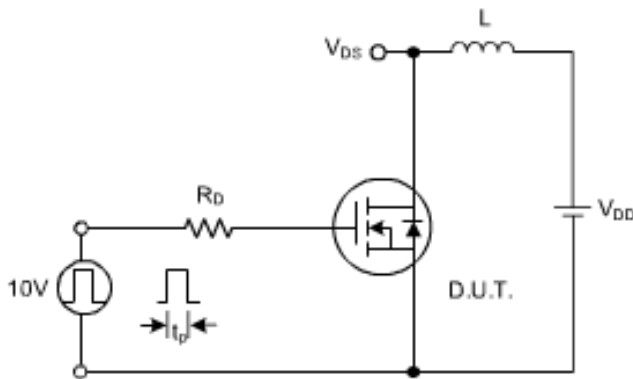


Source-Drain Diode Forward

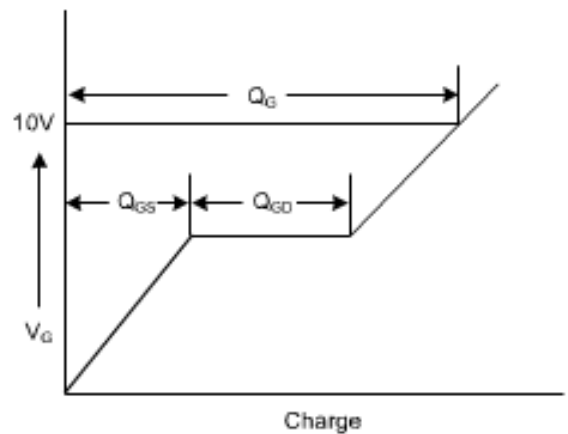
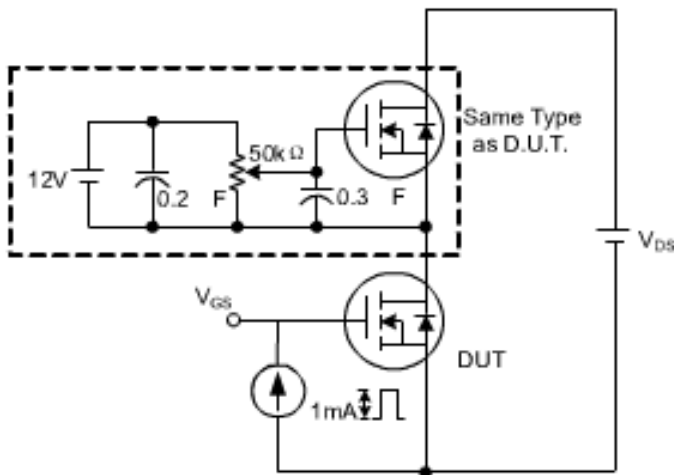


Test Circuits

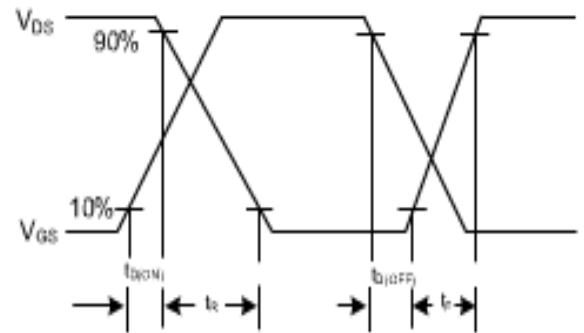
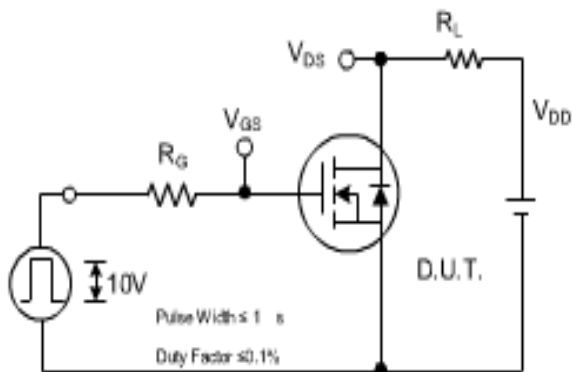
Avalanche test circuits and waveforms



Gate charge test circuits and waveforms



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